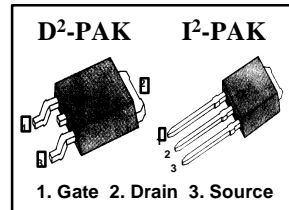


**FEATURES**

- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- 175°C Operating Temperature
- Lower Leakage Current : 10 μA (Max.) @ V<sub>DS</sub> = 60V
- Lower R<sub>DS(ON)</sub> : 0.033 Ω (Typ.)

BV<sub>DSS</sub> = 16 V  
 R<sub>DS(on)</sub> = 0.046 Ω  
 I<sub>D</sub> = 30 A



**Absolute Maximum Ratings**

Symbol	Characteristic	Value	Units
V <sub>DSS</sub>	Drain-to-Source Voltage	60	V
I <sub>D</sub>	Continuous Drain Current (T <sub>C</sub> =25°C)	30	A
	Continuous Drain Current (T <sub>C</sub> =100°C)	21	
I <sub>DM</sub>	Drain Current-Pulsed ①	105	A
V <sub>GS</sub>	Gate-to-Source Voltage	± 20	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy ②	463	mJ
I <sub>AR</sub>	Avalanche Current ①	30	A
E <sub>AR</sub>	Repetitive Avalanche Energy ①	8.3	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.5	V/ns
P <sub>D</sub>	Total Power Dissipation (T <sub>A</sub> =25°C)*	3.8	W
	Total Power Dissipation (T <sub>C</sub> =25°C)	83	W
	Linear Derating Factor	0.55	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	- 55 to +175	°C
T <sub>L</sub>	Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5-seconds	300	

**Thermal Resistance**

Symbol	Characteristic	Typ.	Max.	Units
R <sub>θJC</sub>	Junction-to-Case	--	1.81	°C/W
R <sub>θJA</sub>	Junction-to-Ambient *	--	40	
R <sub>θJA</sub>	Junction-to-Ambient	--	62.5	

\* When mounted on the minimum pad size recommended (PCB Mount).

### Electrical Characteristics ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
$BV_{DSS}$	Drain-Source Breakdown Voltage	60	--	--	V	$V_{GS}=0V, I_D=250\mu\text{A}$
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	0.06	--	V/ $^\circ\text{C}$	$I_D=250\mu\text{A}$ <b>See Fig 7</b>
$V_{GS(th)}$	Gate Threshold Voltage	1.0	--	2.0	V	$V_{DS}=5V, I_D=250\mu\text{A}$
$I_{GSS}$	Gate-Source Leakage , Forward	--	--	100	nA	$V_{GS}=20V$
	Gate-Source Leakage , Reverse	--	--	-100		$V_{GS}=-20V$
$I_{DSS}$	Drain-to-Source Leakage Current	--	--	10	$\mu\text{A}$	$V_{DS}=60V$
		--	--	100		$V_{DS}=48V, T_C=150^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	0.046	$\Omega$	$V_{GS}=5V, I_D=15A$ ④
$g_{fs}$	Forward Transconductance	--	19	--	$\text{S}$	$V_{DS}=30V, I_D=15A$ ④
$C_{iss}$	Input Capacitance	--	970	1260	pF	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$ <b>See Fig 5</b>
$C_{oss}$	Output Capacitance	--	334	385		
$C_{rss}$	Reverse Transfer Capacitance	--	131	150		
$t_{d(on)}$	Turn-On Delay Time	--	13	35	ns	$V_{DD}=30V, I_D=30A,$ $R_G=6\Omega$ <b>See Fig 13</b> ④ ⑤
$t_r$	Rise Time	--	21	55		
$t_{d(off)}$	Turn-Off Delay Time	--	36	80		
$t_f$	Fall Time	--	28	65		
$Q_g$	Total Gate Charge	--	27	35	nC	$V_{DS}=48V, V_{GS}=5V,$ $I_D=30A$ <b>See Fig 6 &amp; Fig 12</b> ④ ⑤
$Q_{gs}$	Gate-Source Charge	--	9	--		
$Q_{gd}$	Gate-Drain( "Miller" ) Charge	--	12	--		

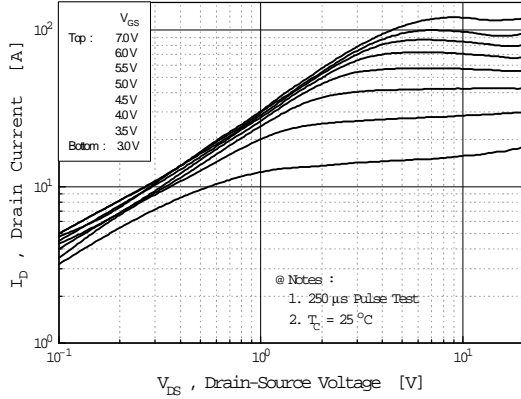
### Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
$I_S$	Continuous Source Current	--	--	30	A	Integral reverse pn-diode in the MOSFET
$I_{SM}$	Pulsed-Source Current ①	--	--	105		
$V_{SD}$	Diode Forward Voltage ④	--	--	1.6	V	$T_J=25^\circ\text{C}, I_S=30A, V_{GS}=0V$
$t_{rr}$	Reverse Recovery Time	--	64	--	ns	$T_J=25^\circ\text{C}, I_F=30A$
$Q_{rr}$	Reverse Recovery Charge	--	0.122	--	$\mu\text{C}$	$di_F/dt=100A/\mu\text{s}$ ④

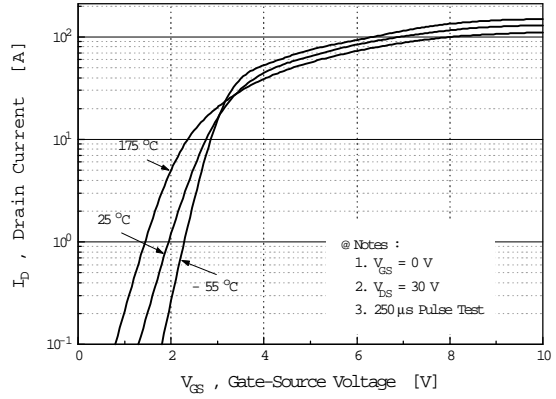
#### Notes ;

- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ②  $L=0.6\text{mH}, I_{AS}=30A, V_{DD}=25V, R_G=27\Omega,$  Starting  $T_J=25^\circ\text{C}$
- ③  $I_{SD} \leq 30A, di/dt \leq 300A/\mu\text{s}, V_{DD} \leq BV_{DSS},$  Starting  $T_J=25^\circ\text{C}$
- ④ Pulse Test : Pulse Width = 250  $\mu\text{s}$ , Duty Cycle  $\leq 2\%$
- ⑤ Essentially Independent of Operating Temperature

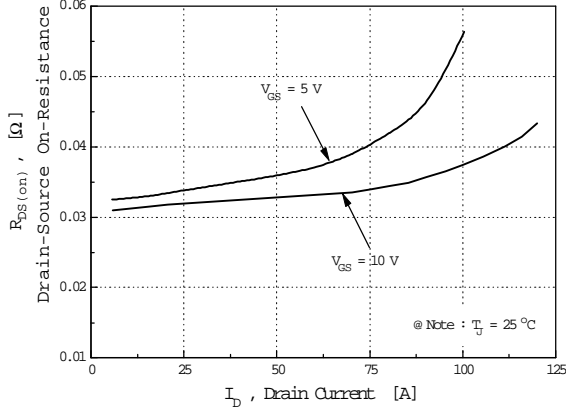
**Fig 1. Output Characteristics**



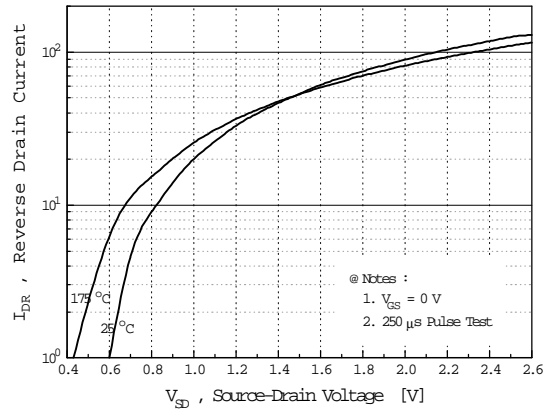
**Fig 2. Transfer Characteristics**



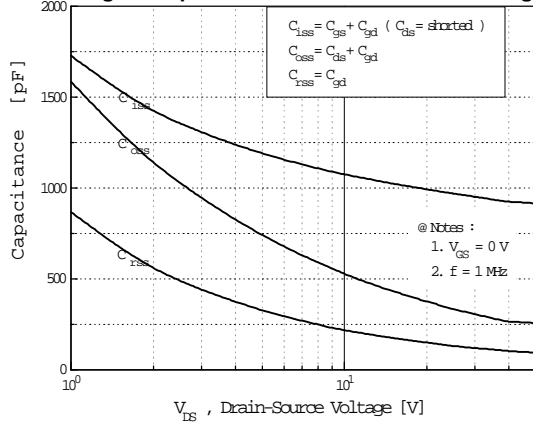
**Fig 3. On-Resistance vs. Drain Current**



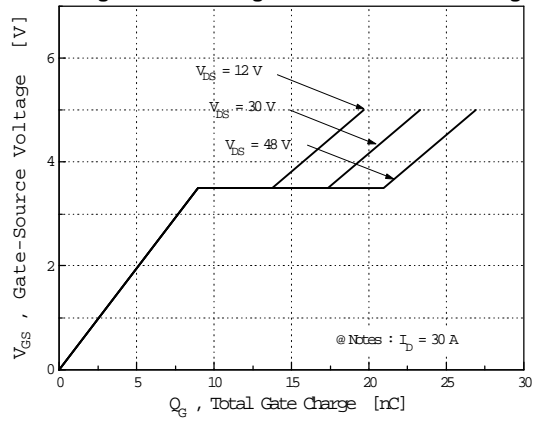
**Fig 4. Source-Drain Diode Forward Voltage**



**Fig 5. Capacitance vs. Drain-Source Voltage**



**Fig 6. Gate Charge vs. Gate-Source Voltage**



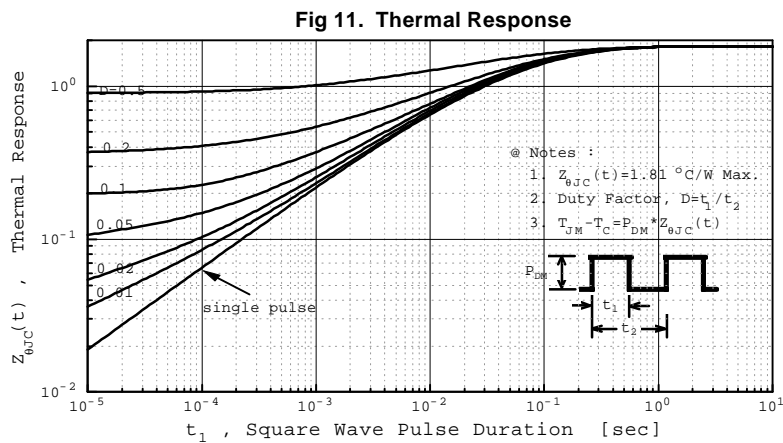
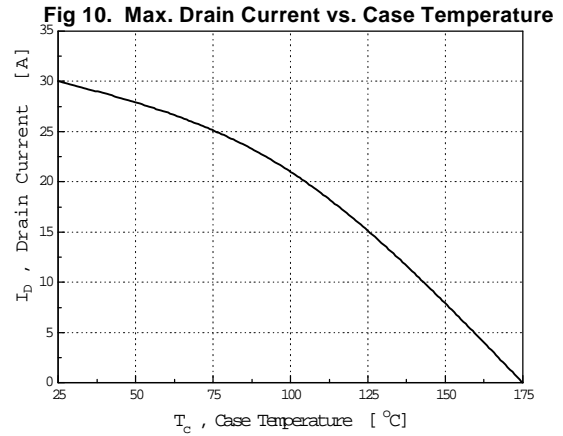
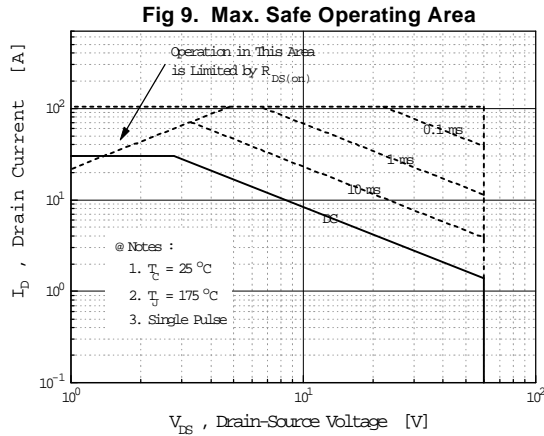
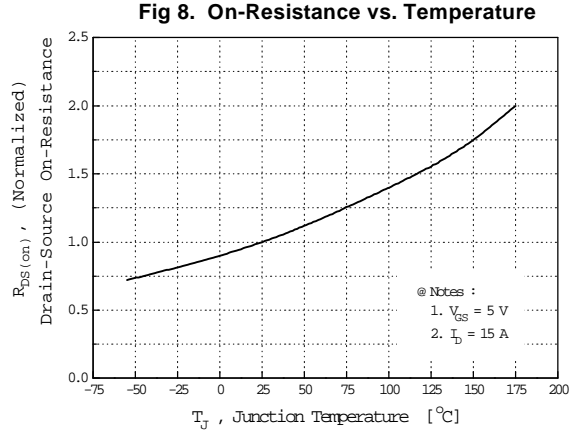
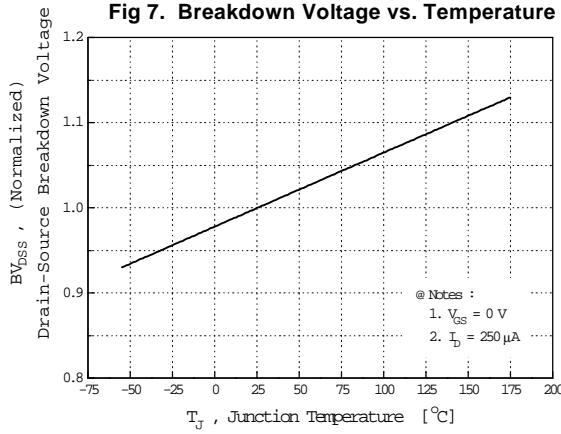


Fig 12. Gate Charge Test Circuit & Waveform

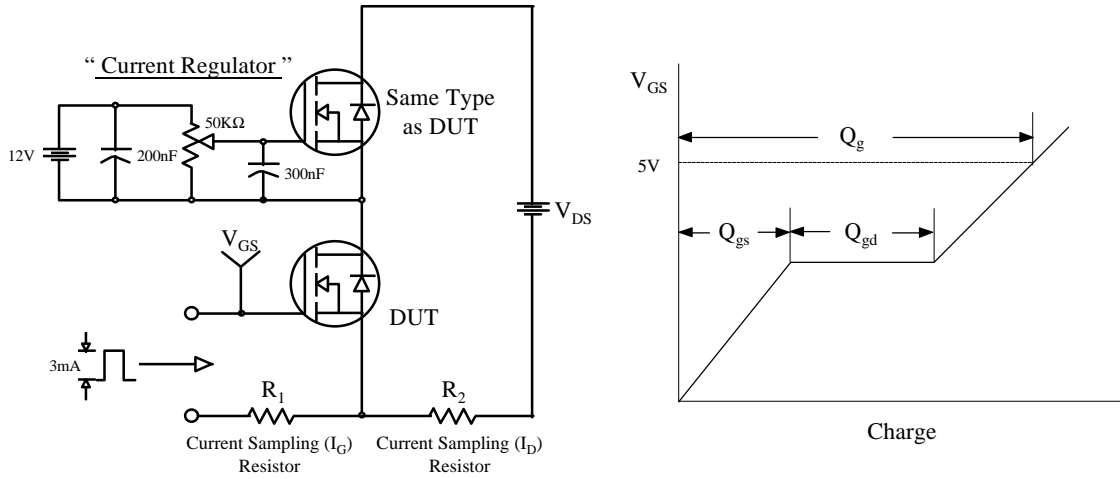


Fig 13. Resistive Switching Test Circuit & Waveforms

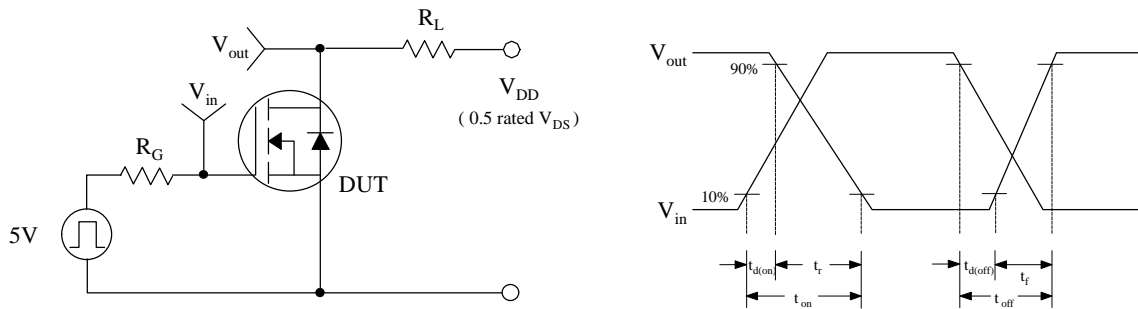


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

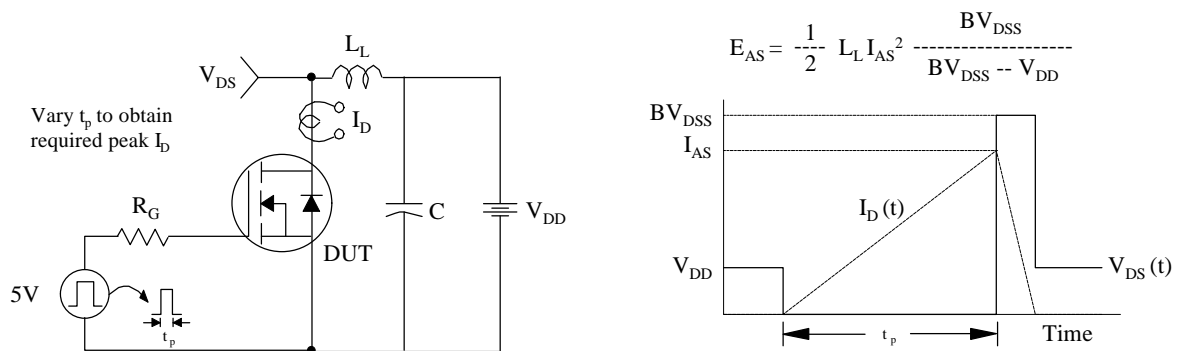


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

